



FDMA6676PZ Information

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For Reference Only

Part Number FDMA6676PZ

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 30V 11A

Package 6-PowerWDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FDMA6676PZ Specifications

Manufacturer Part Number FDMA6676PZ Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 6-PowerWDFN Series PowerTrench? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.6V @ 250µA Gate Charge (Qg) (Max) @ Vgs 46nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2160pF @ 15V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 6-PowerWDFN Series PowerTrench? FET Type P-Channel Technology MOSFET (Metal Oxide) Jorin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Afonc @ 10V Input Capacitance (Ciss) (Max) @ Vds 2160pF @ 15V Vgs (Max) #25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 6-PowerWDFN	Manufacturer Part Number	FDMA6676PZ
Package 6-PowerWDFN Series PowerTrench? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.6V @ 250μA Gate Charge (Qg) (Max) @ Vgs 46nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2160pF @ 15V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN	Manufacturer	Fairchild/ON Semiconductor
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Series PowerTrench? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.6V @ 250μA Gate Charge (Qg) (Max) @ Vgs 46nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2160pF @ 15V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.6V @ 250µA Gate Charge (Qg) (Max) @ Vgs 46nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2160pF @ 15V Vgs (Max) ±25V FET Feature Power Dissipation (Max) 2.4W (Ta) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN	Package	6-PowerWDFN
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature Surplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V 11A (Ta) 4.5V, 10V 2.6V @ 250µA 46nC @ 10V 2160pF @ 15V 225V FET Feature - C Surface Mount 6-MicroFET (2x2) 6-PowerWDFN	Series	PowerTrench?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C11A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.6V @ 250μAGate Charge (Qg) (Max) @ Vgs46nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2160pF @ 15VVgs (Max)±25VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs13.5 mOhm @ 11A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-MicroFET (2x2)Package / Case6-PowerWDFN	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 11A (Ta) 12.6V @ 250μA 10V 2.6V @ 250μA 2160pF @ 15V 2.5V FET Feature	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.6V @ 250μAGate Charge (Qg) (Max) @ Vgs46nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2160pF @ 15VVgs (Max)±25VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs13.5 mOhm @ 11A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-MicroFET (2x2)Package / Case6-PowerWDFN	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 6-PowerWDFN	Current - Continuous Drain (Id) @ 25°C	11A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN	Vgs(th) (Max) @ Id	2.6V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)2.4W (Ta)Rds On (Max) @ Id, Vgs13.5 mOhm @ 11A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-MicroFET (2x2)Package / Case6-PowerWDFN	Gate Charge (Qg) (Max) @ Vgs	46nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	2160pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13.5 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs13.5 mOhm @ 11A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-MicroFET (2x2)Package / Case6-PowerWDFN	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN	Power Dissipation (Max)	2.4W (Ta)
Mounting TypeSurface MountSupplier Device Package6-MicroFET (2x2)Package / Case6-PowerWDFN	Rds On (Max) @ Id, Vgs	13.5 mOhm @ 11A, 10V
Supplier Device Package 6-MicroFET (2x2) Package / Case 6-PowerWDFN	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 6-PowerWDFN	Mounting Type	Surface Mount
	Supplier Device Package	6-MicroFET (2x2)
Report errors?	Package / Case	6-PowerWDFN
		Report errors?

FDMA6676PZ Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDMA6676PZ Payment Methods



















FDMA6676PZ Shipping Methods













If you have any question about FDMA6676PZ, please do not hesitate to contact us!

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